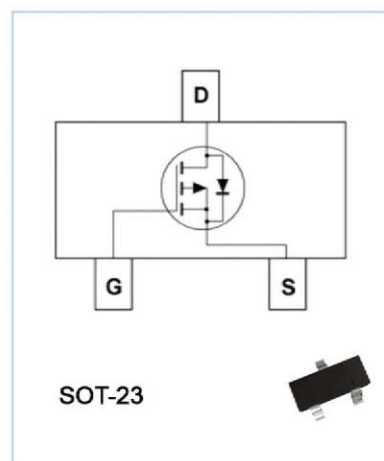


P-Channel Enhancement Mode MOSFET Feature

- -50V/-0.13A, $R_{DS(ON)} = 10\ \Omega$ (MAX) @ $V_{GS} = -5V$, $I_{DS} = -0.1A$
- Super High dense cell design for extremely low $R_{DS(ON)}$
- Reliable and Rugged
- SOT-23 for Surface Mount Package



Applications

- Power Management
Portable Equipment and Battery Powered Systems.

Absolute Maximum Ratings

$T_A = 25^\circ\text{C}$ Unless Otherwise noted

Parameter	Symbol	Limit	Units
Drain-Source Voltage	V_{DS}	-50	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	-0.13	A

Electrical Characteristics

$T_A = 25^\circ\text{C}$ Unless Otherwise noted

Parameter	Symbol	Test Conditions	Min	Typ.	Max	Units
Off Characteristics						
Drain to Source Breakdown Voltage	BVDSS	$V_{GS} = 0V$, $I_D = -250\mu A$	-50	-	-	V
Zero-Gate Voltage Drain Current	IDSS	$V_{DS} = -50V$, $V_{GS} = 0V$	-	-	-15	μA
Gate Body Leakage Current, Forward	IGSSF	$V_{GS} = 20V$, $V_{DS} = 0V$	-	-	100	nA
Gate Body Leakage Current, Reverse	IGSSR	$V_{GS} = -20V$, $V_{DS} = 0V$	-	-	-100	nA
On Characteristics						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS} = V_{DS}$, $I_D = -1mA$	-0.8	-	-2.5	V
Static Drain-source On-Resistance	$R_{DS(ON)}$	$V_{GS} = -5V$, $I_D = -0.1A$	-	5	10	Ω
Drain-Source Diode Characteristics and Maximum Ratings						
Drain-Source Diode Forward Voltage	VSD	$V_{GS} = 0V$, $I_S = -0.13A$			-2.5	V

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DYNAMIC PARAMETERS						
Input Capacitance	Ciss	VGS=0V, VDS=-5V, f=1MHz		30		pF
Output Capacitance	Coss			10		pF
Reverse Transfer Capacitance	Crss			5		pF
SWITCHING PARAMETERS						
Turn-On Delay Time	tD(on)	VGS=-10V, VDS=-15V, ID=-0.25A, RL=50 Ω		2.5		ns
Turn-On Rise Time	tr			1.0		ns
Turn-Off Delay Time	tD(off)			16		ns
Turn-Off Fall Time	tr			8		ns

Typical Characteristics

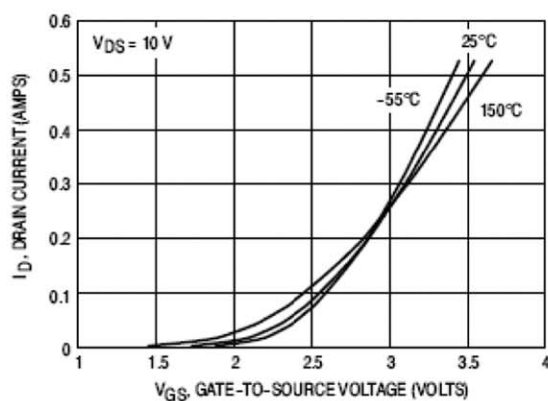


Figure 1. Transfer Characteristics

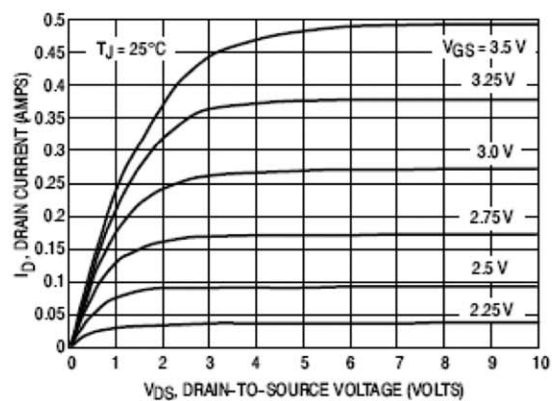


Figure 2. On-Region Characteristics

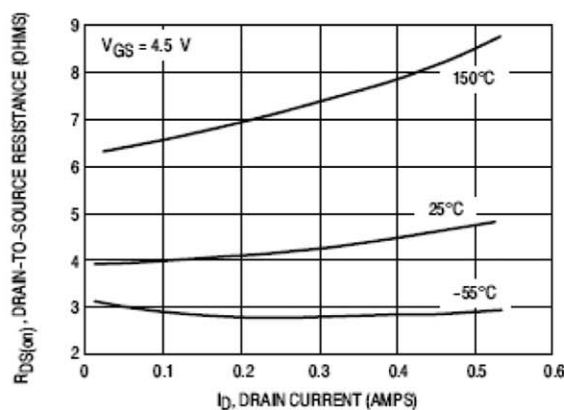


Figure 3. On-Resistance versus Drain Current

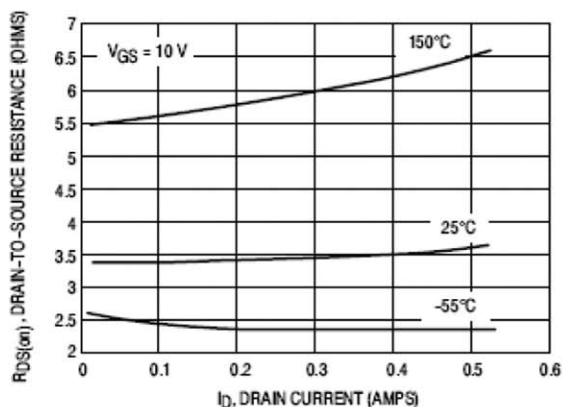


Figure 4. On-Resistance versus Drain Current

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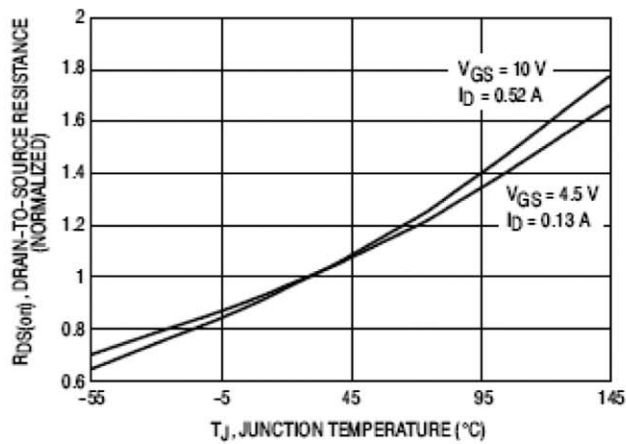


Figure 5. On-Resistance Variation with Temperature

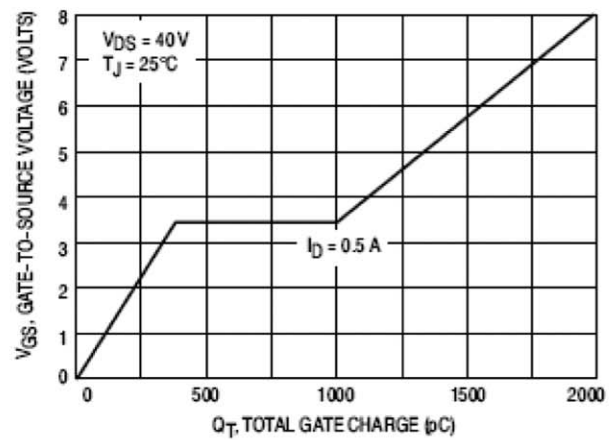


Figure 6. Gate Charge

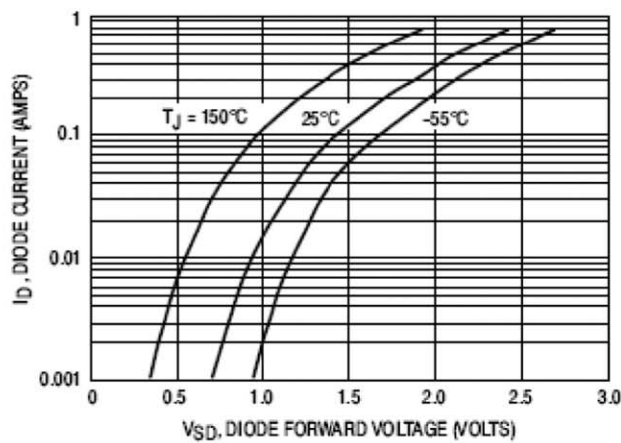
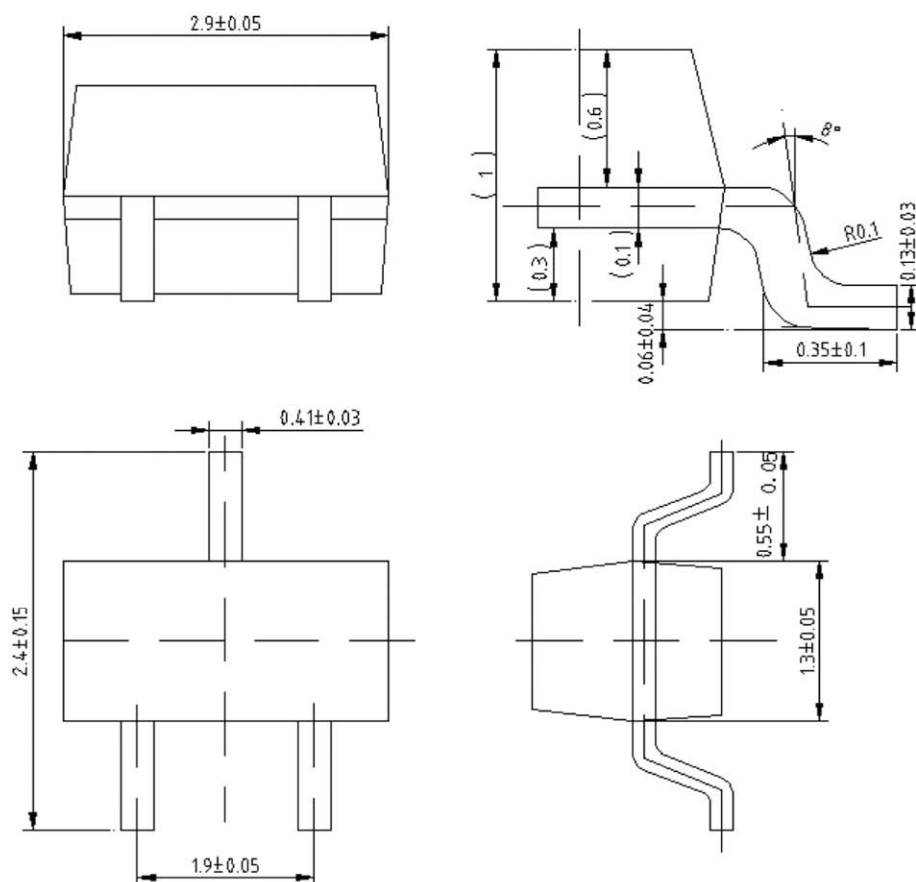


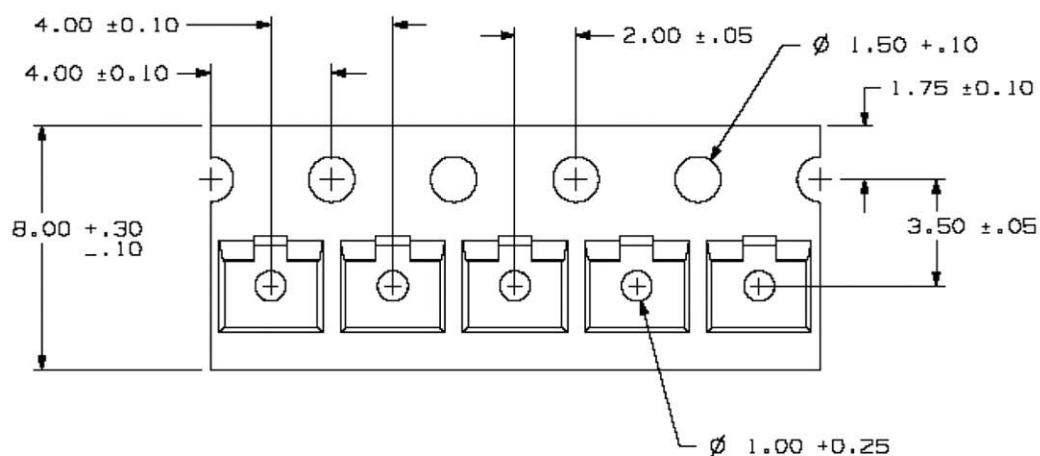
Figure 7. Body Diode Forward Voltage



SOT-23 Package Outline Dimensions (UNIT: mm)



SOT-23 Carrier Tape



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